

## 2.5 $\Omega$ , High Bandwidth, Dual SPDT Analog Switch

#### **DESCRIPTION**

The DG2032E is a low-voltage dual single-pole / double-throw monolithic CMOS analog switch. Designed to operate from 1.8 V to 5.5 V power supply, the DG2032E achieves a bandwidth of 221 MHz while providing low on-resistance (2.5  $\Omega$ ), excellent on-resistance matching (0.3  $\Omega$ ) and flatness (1  $\Omega$ ) over the entire signal range.

The DG2032E offers the advantage of high linearity that reduces signal distortion, making ideal for audio, video, and USB signal routing applications.

Built on Vishay Siliconix's proprietary sub-micron high-density process, the DG2032E brings low power consumption at the same time as reduces PCB spacing with the QFN12 package.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. The QFN12 package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free "-GE4" suffix. The nickel-palladium-gold device terminations meet all JEDEC® standards for reflow and MSL ratings.

#### **FEATURES**

- 1.8 V to 5.5 V single supply operation
- Low R<sub>ON</sub>: 2.5 Ω at 4.5 V
- 221 MHz. -3 dB bandwidth
- Low off-isolation, -58 dB at 1 MHz
- +1.6 V logic compatible
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

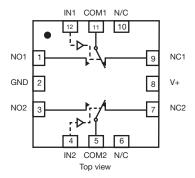
#### **BENEFITS**

- · High linearity
- Low power consumption
- High bandwidth
- Full rail signal swing range

#### **APPLICATIONS**

- USB / UART signal switching
- · Audio / video switching
- Cellular phone
- Media players
- Modems
- Hard drives
- PCMCIA

#### **FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION**



TRUTH TABLE							
LOGIC	NC1 AND NC2	NO1 AND NO2					
0	ON	OFF					
1	OFF	ON					

ORDERING INFORMATION							
TEMP. RANGE	PACKAGE	PART NUMBER					
-40 °C to +85 °C	12-Pin QFN (3 mm x 3 mm)	DG2032EDN-T1-GE4					

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	LIMIT	UNIT					
Reference to GND	<u> </u>						
V+		-0.3 to +6	V				
IN, COM, NC, NO <sup>a</sup>		-0.3 to (V+ + 0.3)	v				
Continuous current (any terminal)	± 50	mA					
Peak current (pulsed at 1 ms, 10 % duty of	± 200	IIIA					
Storage temperature (D suffix)		-65 to +150	°C				
Power dissipation (packages) b	12-Pin QFN (3 mm x 3 mm) <sup>c</sup>	1295	mW				
ESD / HBM	EIA / JESD22-A114-A	7.5k	V				
ESD / CDM	EIA / JESD22-C101-A	1.5k	v				
Latch up	JESD78	300	mA				

#### Notes

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings
- b. All leads welded or soldered to PC board
- c. Derate 4 mW/°C above 70 °C



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SPECIFICATIONS (V+ = 3 V)								
PARAMETER	SYMBOL	TEST CONDITIONS OTHERWISE UNLESS SPECIFIED		TEMP.	LIMITS -40 °C to +85 °C			UNIT
		$V+ = 3 V, \pm 10 \%, V_{INL} = 0.5 V, V_{INH}$	<sub>H</sub> = 1.5 V <sup>e</sup>		MIN. c	TYP. b	MAX. c	
Analog Switch								
Analog signal range <sup>d</sup>	$V_{ANALOG}$			Full	0	-	V+	V
		$V+ = 1.8 \text{ V}, V_{NC/NO} = 0.4 \text{ V} / V+, I_{NC/NO}$	", – 8 m∆	Room	-	7	11	
Drain-source on-resistance	R <sub>DS(on)</sub>	V1 = 1.5 V, V <sub>NC/NO</sub> = 0.4 V / V1, I <sub>NC/NO</sub> = 0.111/V		Full	-	-	13	
Brain coarce on recictance	1 1DS(0H)	V+ = 2.7 V, V <sub>COM</sub> = 0.8 V / 1.8 V, I <sub>COM</sub> = 10 mA		Room	-	4.6	5.5	
		V = 2.7 V, VCOIN = 0.0 V / 1.0 V, ICO	IVI — TO THE	Full	-	-	6.5	Ω
On-resistance matching	$\Delta R_{DS(on)}$			Room	-	0.02	0.3	
on redictaries matering	21 (DS(0H)	$V+ = 2.7 \text{ V}, V_{COM} = 0.8 \text{ V} / 1.4 \text{ V}$	/ 1.8 V,	Full	-	-	0.6	
On-resistance flatness d, f	R <sub>flat(on)</sub>	I <sub>COM</sub> = 10 mA		Room	-	0.62	1	
On resistance namess	i itlat(on)			Full	-	-	1.5	
Off leakage current <sup>g</sup>	hiomores	$V+ = 3.6 \text{ V}, V_{NC/NO} = 1 \text{ V} / 3.2$	2 V,	Room	-1	0.01	1	
On leakage current •	I <sub>NC/NO(off)</sub>	V <sub>COM</sub> = 3.2 V / 1 V		Full	-5	-	5	nA
Channel-on leakage	loove v	$V_{+} = 3.3 \text{ V}, V_{COM} = V_{NC/NO} = 1 \text{ V}$	/32V	Room	-1	0.01	1	ΠA
current <sup>g</sup>	I <sub>COM(on)</sub>	V+ = 3.3 V, VCOM = VNC/NO = 1 V	/ J.Z V	Full	-5	ı	5	
Digital Control								
Input current <sup>d</sup>	$I_{INL}$ or $I_{INH}$			Full	-1	-	1	μΑ
Input high voltage <sup>d</sup>	$V_{INH}$			Full	1.5	ı	ı	V
Input low voltage <sup>d</sup>	$V_{INL}$			Full	ı	ı	0.4	V
Digital input capacitance <sup>d</sup>	$C_{IN}$			Room	-	3	ı	pF
Dynamic Characteristics								
Turn-on time	+			Room	ı	19	45	
rum-on time	t <sub>ON</sub>	$V_{NC/NO} = 3 \text{ V, } C_1 = 35 \text{ pF, } R_1 = 300 \Omega$		Full	-	-	50	
Turn-off time	t <sub>OFF</sub>			Room	-	9	35	
rum-on time		V <sub>NC/NO</sub> = 3 V, O <sub>L</sub> = 33 βr, n <sub>L</sub> =	300 12	Full	ı	ı	45	ns
Break-before-make time d				Room	4	11	ı	]
break-before-make time	t <sub>BBM</sub>			Full	3	1	ı	
Charge injection <sup>d</sup>	$Q_{INJ}$	C <sub>L</sub> = 1 nF, V <sub>gen</sub> = 1.5 V, R <sub>gen</sub> =	= 0 Ω	Room	ı	-9	ı	рС
Bandwidth <sup>d</sup>	BW	C <sub>L</sub> = 5 pF (set up capacitano	ce)	Room	-	226	ı	MHz
Off-isolation d	OIRR	D = 50 0 C = 5 pE	f = 1 MHz	Room	-	-55	-	
OII-ISOIAtIOII 9		$R_L = 50 \Omega$ , $C_L = 5 pF$	= 10 MHz	Room	-	-42	-	dB
Character to alcount an actual d		D 5000 5 75	f = 1 MHz	Room	-	-61	-	иь
Channel-to-channel crosstalk d	X <sub>TALK</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$	= 10 MHz	Room	-	-44	-	
NO, NC off capacitance d	C <sub>NO(off)</sub>	V+ = 2.7 V, f = 1 MHz		Room	-	7	-	
NO, NC on capacitance	C <sub>NC(off)</sub>			Room	-	7	-	pF
Channel-on capacitance d	C <sub>NO(on)</sub>			Room	-	23	-	
опаппет-оп сарасітапсе <sup>ч</sup>	C <sub>NC(on)</sub>			Room	-	23	1	
Power Supply								
Power supply range	V+ 2.7 - 3.3 V					V		
1 ower supply range								

#### Notes

- a. Room = 25 °C, Full = as determined by the operating suffix
- b. Typical values are for design aid only, not guaranteed nor subject to production testing
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- d. Guarantee by design, not subjected to production test
- e.  $V_{IN}$  = input voltage to perform proper function
- f. Difference of min. and max. values
- g. Guaranteed by 5 V testing

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PARAMETER	SYMBOL	TEST CONDITIONS OTHERWISE UNLESS SPE	TEMP.	LIMITS -40 °C to +85 °C			UNIT	
		$V+ = 5 V, \pm 10 \%, V_{INL} = 0.5 V, V_{INL} = 0.5 V$	V <sub>INH</sub> = 2 V <sup>e</sup>	a	MIN. c	TYP. b	MAX. c	
Analog Switch								
Analog signal range d	V <sub>ANALOG</sub>			Full	0	-	V+	V
Drain-source on-resistance	D	$V + = 4.5 \text{ V}, V_{COM} = 0.8 \text{ V} / 3.5 \text{ V}; I_{COM} = 0.8 \text{ V}; I_{COM} = 0.8 \text{ V} / 3.5 $	= 10 mA	Room	-	2.5	3.1	
Diani-source on-resistance	R <sub>DS(on)</sub>	V+ = 4.5 V, V <sub>COM</sub> = 0.8 V / 3.5 V, I <sub>C</sub>	COM = TOTTIA	Full	-	-	4	
On-resistance matching	$\Delta R_{DS(on)}$			Room	-	0.01	0.4	Ω
On resistance matering	Zi iDS(on)	$V+ = 4.5 \text{ V}, V_{COM} = 0.8 \text{ V} / 2.5 \text{ V} / 3.5 \text{ V},$		Full	-	-	0.6	5.2
On-resistance flatness d, f	R <sub>flat(on)</sub>	$I_{COM} = 10 \text{ mA}$		Room	-	0.61	1	
on resistance names	· ·liat(on)			Full	-	-	1.5	
Off leakage current <sup>g</sup>	I <sub>NC/NO(off)</sub>	$V+ = 5.5 V, V_{NC/NO} = 1 V /$	4.5 V,	Room	-2	0.15	2	
	110/110(011)	$V_{COM} = 4.5 \text{ V} / 1 \text{ V}$		Full	-10	-	10	nA
Channel-on leakage current <sup>g</sup>	I <sub>COM(on)</sub>	$V+ = 5.5 \text{ V}, V_{COM} = V_{NC/NO} = 1$	V / 4.5 V	Room	-2	0.20	2	
	-COM(OH)	110,110		Full	-10	-	10	
		$V+ = 0 V, V_{COM} = 5.5 V, NC/N$		Full	-	0.01	5	μΑ
Power down leakage <sup>d</sup>	I <sub>PD</sub>	$V+=0$ V, $V_{NC/NO}=5.5$ COM, open	Full	-	0.01	3	mA	
Digital Control								
Input current d	I <sub>INL</sub> or I <sub>INH</sub>			Full	-1	-	1	μΑ
Input high voltage d	V <sub>INH</sub>			Full	2	-	-	V
Input low voltage d	$V_{INL}$			Full	-	-	0.5	V
Digital input capacitance d	$C_{IN}$			Room	-	3	-	pF
Dynamic Characteristics								
Turn-on time	t			Room	-	13	40	
Turri-ori time	t <sub>ON</sub>			Full	-	-	43	2 20
Turn-off time	t	V 3 V. C 35 pF. R.	- 300 O	Room	-	7	33	
Turn-on time	t <sub>OFF</sub>	VNC/NO = 3 V, OL = 33 pr , Til	$V_{NC/NO} = 3 \text{ V}, C_L = 35 \text{ pF}, R_L = 300 \Omega$		-	-	35	ns
Break-before-make time d	tone			Room	3	6	-	]
	t <sub>BBM</sub>			Full	2	-	-	
Propagation delay <sup>d</sup>	tpd	$V+ = 5 V$ , no $R_L$		Room	-	380	-	ps
Charge injection d	$Q_{INJ}$	$C_L = 1 \text{ nF}, V_{gen} = 2.5 \text{ V}, R_{ge}$	$_{n} = 0 \Omega$	Room	-	-19.4	-	рC
Bandwidth <sup>d</sup>	BW	C <sub>L</sub> = 5 pF (set up capacita	ance)	Room	-	221	-	MHz
Off-isolation d	OIRR	$R_1 = 50 \Omega$ , $C_1 = 5 pF$	f = 1 MHz	Room	-	-58	-	
C. ISSIGNOTI		11 00 22, 0[ - 0 β1	f = 10 MHz	Room	-	-43	-	dB
Channel-to-channel	X <sub>TALK</sub>	$R_1 = 50 \Omega$ , $C_1 = 5 pF$	f = 1 MHz	Room	-	-62	-	ab
crosstalk <sup>d</sup>		1 1 = 00 12, 0 = 0 pi	f = 10 MHz	Room	-	-47	-	
NO, NC off capacitance d	$C_{NO(off)}$	V+ = 5 V, f = 1 MHz		Room	-	7	-	pF
140, 140 on capacitance	$C_{NC(off)}$			Room		7	-	
Channel-on capacitance d	$C_{NO(on)}$			Room	-	23	-	
·	C <sub>NC(on)</sub>			Room	-	23	-	
Power Supply		_						
Power supply range	V+				4.5	=.	5.5	V
Power supply current <sup>d</sup>	l+	$V+ = 5.5 \text{ V}, V_{IN} = 0 \text{ V or } 5$	Full	-	-	1	μΑ	

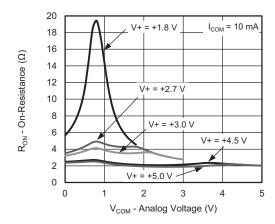
#### Notes

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- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- d. Guarantee by design, not subjected to production test
- e.  $V_{IN}$  = input voltage to perform proper function
- f. Difference of min. and max. values
- g. Guaranteed by 5 V testing

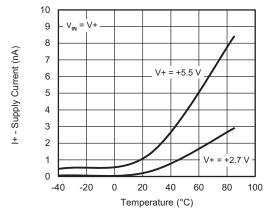
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



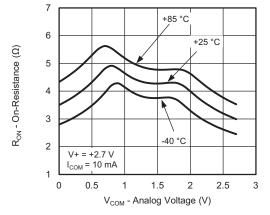
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



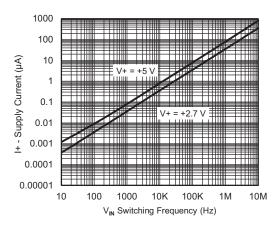
R<sub>ON</sub> vs. V<sub>COM</sub> and Single Supply Voltage



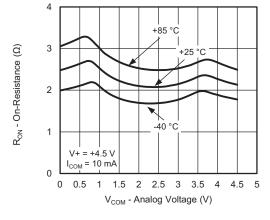
**Supply Current vs. Temperature** 



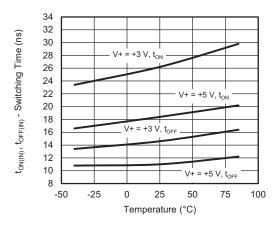
R<sub>ON</sub> vs. Analog Voltage and Temperature



**Positive Supply Current vs. Switching Frequency** 



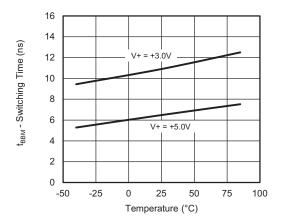
R<sub>ON</sub> vs. Analog Voltage and Temperature



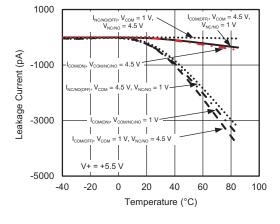
**Switching Time vs. Temperature** 



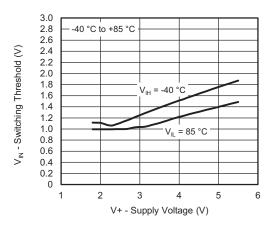
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



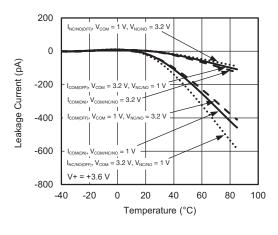
Switching Time vs. Temperature



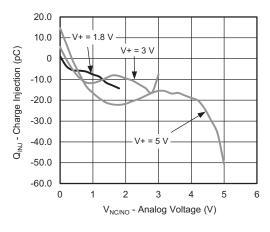
Leakage Current vs. Temperature



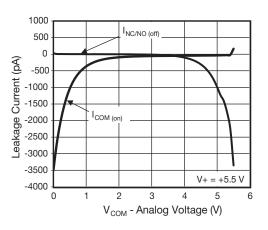
Switching Threshold vs. Supply Voltage



Leakage Current vs. Temperature



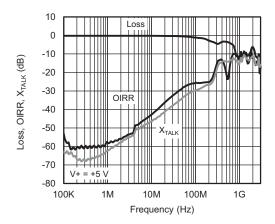
Charge Injection vs. Source Voltage



Leakage Current vs. Analog Voltage



### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Loss, OIRR, X<sub>TALK</sub> vs. Frequency

#### **TEST CIRCUITS**

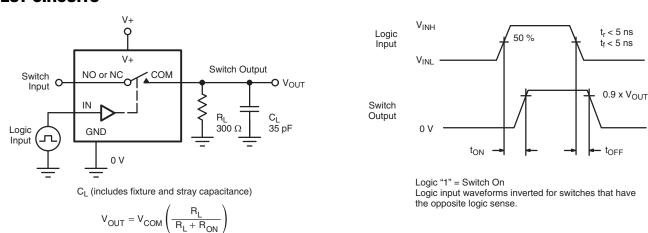


Fig. 1 - Switching Time

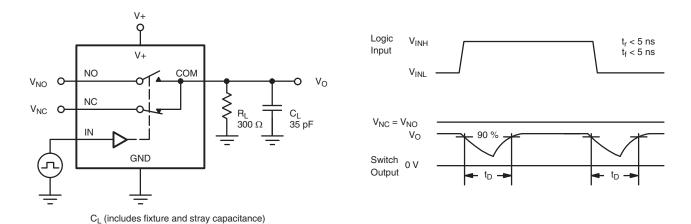
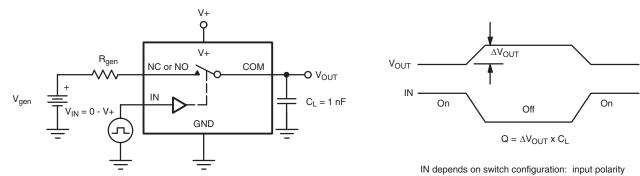


Fig. 2 - Break-Before-Make Interval

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#### **TEST CIRCUITS**



determined by sense of switch.

Fig. 3 - Charge Injection

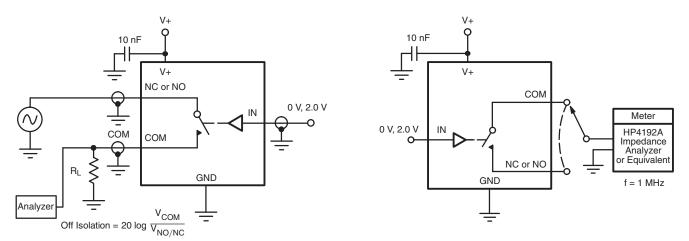


Fig. 4 - Off-Isolation

Fig. 5 - Channel Off / On Capacitance

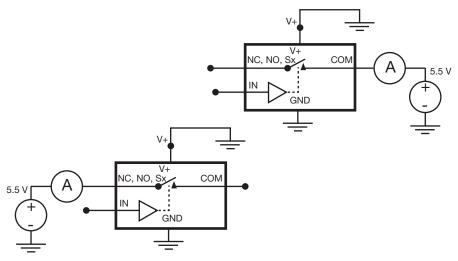
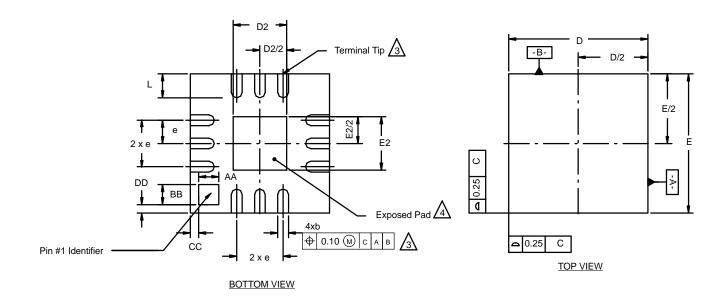


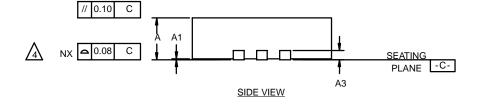
Fig. 6 - Source / Drain Power Down Leakage

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg278604">www.vishay.com/ppg278604</a>.



### QFN-12 LEAD (3 X 3)





#### NOTES:

- 1. All dimensions are in millimeters.
- 2. N is the total number of terminals.

/3.\

Dimension b applies to metallized terminal and is measured between 0.25 and 0.30 mm from terminal tip.  $\,$ 

4.

Coplanarity applies to the exposed heat sink slug as well as the terminal.

The pin #1 identifier may be either a mold or marked feature, it must be located within the zone iindicated.

	МІ	LLIMETE	RS					
Dim	Min	Nom	Max	Min	Nom	Max		
Α	0.80	0.90	1.00	0.032	0.035	0.039		
b	0.18	0.23	0.30	0.007	0.009	0.012		
D		3.00 BSC			0.118 BSC			
D2	1.00	1.15	1.25	0.039 0.045 0.04				
E		3.00 BSC		0.118 BSC				
E2	1.00	1.15	1.25	0.039	0.045	0.049		
е		0.50 BSC		0.02 BSC				
L	0.45	0.55	0.65	0.018	0.022	0.026		
AA	0.435 0.017							
BB		0.435		0.017				
CC		0.18		0.007				
DD	0.18 0.007							
ECN: C-03092—Rev. A, 14-Apr-03 DWG: 5898								

Document Number: 72209

14-Apr-03

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